

# MICROWAVE POWER GAN AMPLIFIER

TGM9398-25

### **FEATURES**

**BROAD BAND 2-STAGE AMPLIFIER** 

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

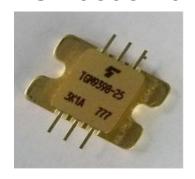
·HIGH POWER

Pout= 44.0dBm at Pin= 23.0dBm

·HIGH GAIN

GL= 24dB(Typ) at Pin= 7dBm

·HERMETICALLY SEALED PACKAGE



# RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power	Pout	VDD1,VDD2= 24V IDDset= 1.2A @Pin= 23.0dBm f = 9.3 to 9.8GHz	dBm	43.0	44.0	_
Drain Current	IDD*		Α	_	2.6	3.5
Power Added Efficiency	ηadd		%	_	38	_
Linear Gain	GL	@Pin= 7dBm	dB	20	24	_

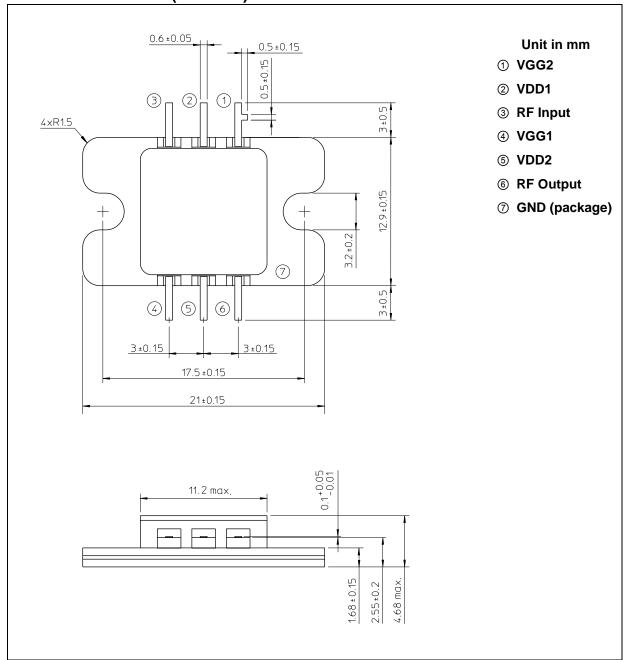
<sup>\*</sup>IDD=IDD1+ IDD2

# ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING	
Drain- Source Voltage	VDD1, VDD2	V	50	
Gate- Source Voltage	VGG1,VGG2	V	-10	
	IDD1	А	1.25	
Drain Current	IDD2	А	7.5	
Flange Temperature	Tf	°C	-40 to +90	
Input Power	Pin	dBm	+27	
Storage Temperature	Tstg	°C	-65 to +175	

<sup>◆</sup> The information contained herein is presented as guidance for product use. No responsibility is assumed by TOSHIBA INFRASTRUCTURE SYSTEMS & SOLUTIONS CORPORATION (hereinafter, referred to as "TISS") for any infringement of patents or any other intellectual property rights of third parties that may result from the use of product. No license to any intellectual property right is granted by this document. The information contained herein is subject to change without prior notice. It is advisable to contact TISS before proceeding with design of equipment incorporating this product.

# PACKAGE OUTLINE (7-BA42B)



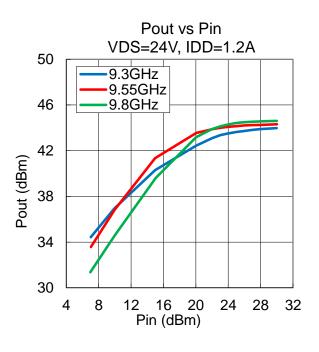
## HANDLING PRECAUTIONS FOR PACKAGE MODEL

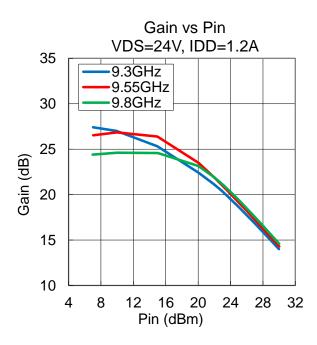
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds 350°C. Flanges of devices should be attached using screws and washers. Recommended torque is 0.18-0.20 N·m.

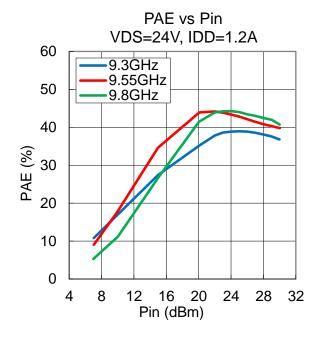
## MICROWAVE SEMICONDUCTOR TECHNICAL DATA

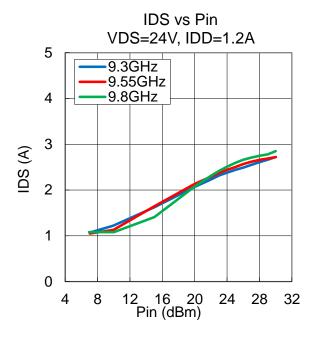
·Pout, Gain, PAE, IDS vs. Pin

VDS= 24 V, IDDset= 1.2 A, f= 9.3, 9.55, 9.8 GHz, Ta= +25 °C





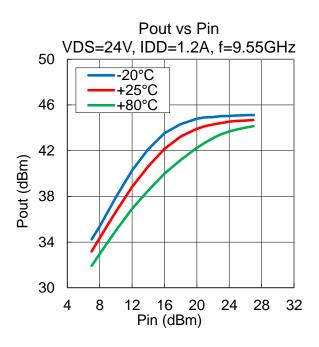


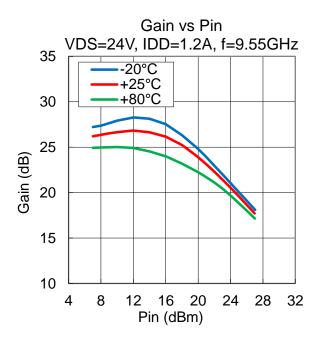


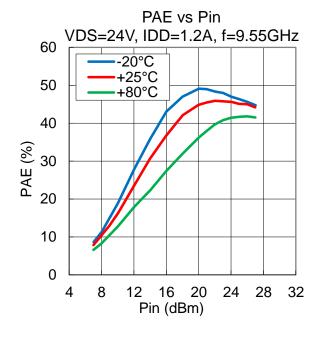
#### MICROWAVE SEMICONDUCTOR TECHNICAL DATA

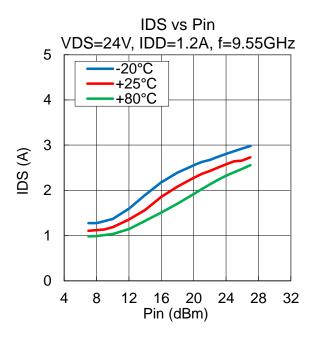
#### ·Pout , Gain , PAE , IDS vs. Pin vs. Temperature

VDS= 24 V, IDDset= 1.2 A, f= 9.55 GHz, Ta= -20, +25, +80 °C



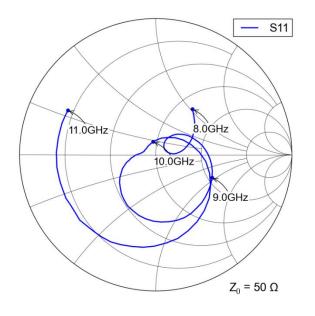


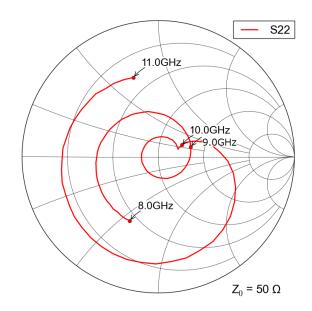


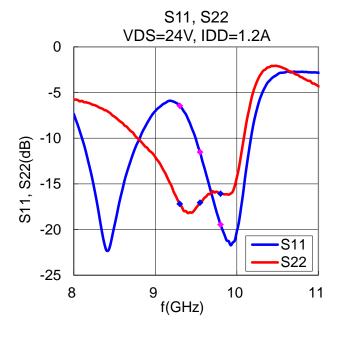


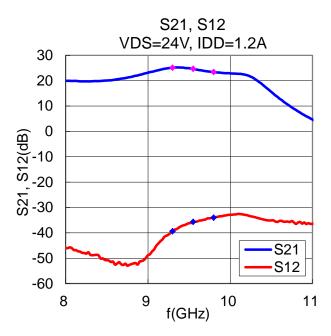
#### -S-Parameters

VDS= 24 V, IDDset= 1.2 A, f= 8.0 to 11.0 GHz, Ta= +25 °C





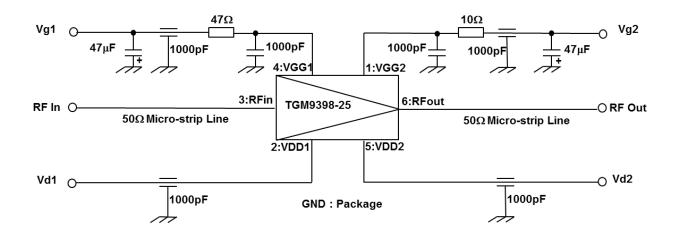






## MICROWAVE SEMICONDUCTOR TECHNICAL DATA

## **MEASUREMENT CIRCUIT SCHEMATIC**





# MICROWAVE POWER GaN AMPLIFIER TGM9398-25

#### MICROWAVE SEMICONDUCTOR TECHNICAL DATA

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Page: **7/7**